

**IN THE CLAIMS:**

**Please enter the following amended claims:**

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1. (Currently Amended) A method of forming a film, comprising the steps of:
- (a) starting a supply of a reaction gas at a first flow rate into a chamber in which a plasma is formed, such that an initial film is formed on a center region of a wafer via a first nozzle provided on the chamber above the center region of the wafer; and
- (b) starting a supply of the reaction gas at a second flow rate into the chamber in which the plasma is formed, after said step (a), while the supply of the reaction gas at said first flow rate continues such that the film is formed on the initial film, the first flow rate being smaller than the second flow rate.
2. (Original) The method according to claim 1, wherein said reaction gas is a compound gas containing Si.
3. (Original) The method according to claim 2, wherein said reaction gas is one of SiH<sub>4</sub>, SiF<sub>4</sub> and TEOS.
4. (Original) The method according to claim 1, wherein said step (b) is carried out 1 to 10 seconds after said step (a) is carried out.

5. (Original) The method according to claim 1, wherein said first flow rate is in a range of one fifth to one tenth of said second flow rate.

6. (Canceled)

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7. (Original) The method according to claim 1, wherein said step (b) comprises the step of:  
starting supply of the reaction gas at the second flow rate into the chamber via second nozzles, and

said second nozzles are provided on side walls of the chamber above the wafer.

8. (Previously Amended) A method of forming a film, comprising the steps of:

(a) forming a film from a center region of a wafer by supplying a reaction gas at a first flow rate, while a thickness of the film is equal to or thinner than 10 nm; and

(b) forming the film on said wafer, by starting to supply the reaction gas at a second flow rate, after said step (a), while continuing to supply the reaction gas at said first flow rate.

9. (Previously Amended) The method according to claim 8, wherein said first flow rate is in a range of one fifth to one tenth of said second flow rate.

10. (Original) The method according to claim 8, wherein said reaction gas is a compound gas containing Si.

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11. (Original) The method according to claim 10, wherein said reaction gas is one of SiH<sub>4</sub>, SiF<sub>4</sub> and TEOS.

12. (Original) The method according to claim 8, wherein said step (b) is carried out 1 to 10 seconds after said step (a) is carried out.

13. (Original) The method according to claim 8, wherein said step (a) comprises the step of:

starting supply of the reaction gas at the first flow rate into the chamber via a first nozzle, and

said first nozzle is provided on the chamber above a center region of the wafer.

14. (Original) The method according to claim 8, wherein said step (b) comprises the step of:

starting supply of the reaction gas at the second flow rate into the chamber via second nozzles, and

said second nozzles are provided on side walls of the chamber above the wafer.

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